

Silicon NPN Power Transistors

2SC4161

DESCRIPTION

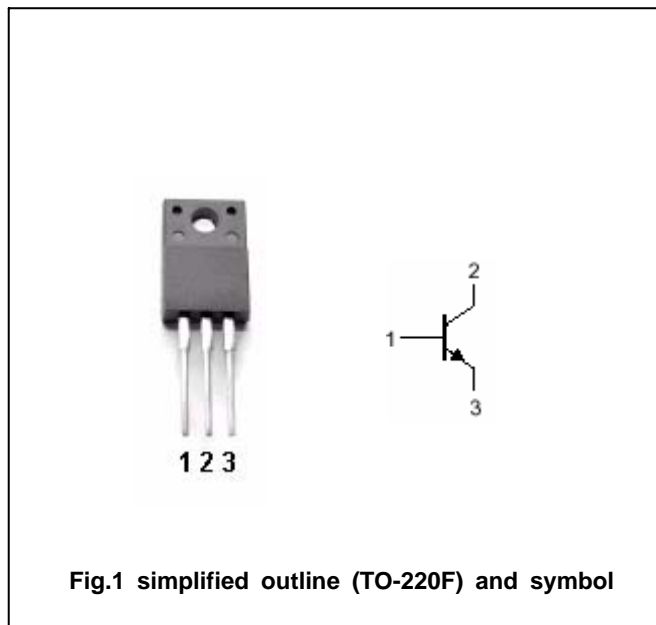
- With TO-220F package
- High breakdown voltage.
- High reliability.
- Fast switching speed

APPLICATIONS

- Switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		14	A
I_B	Base current		3	A
P_C	Collector dissipation	$T_C=25$	30	W
			2	
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =5mA ; R _{BE} =	400			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	500			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A ; I _B =0.8A			0.8	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A ; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =400V ; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			10	μA
h _{FE-1}	DC current gain	I _C =0.8A ; V _{CE} =5V	15		50	
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =5V	10			
h _{FE-3}	DC current gain	I _C =10mA ; V _{CE} =5V	10			
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V ; f=1MHz		80		pF
f _T	Transition frequency	I _C =0.8A ; V _{CE} =10V		20		MHz

Switching times

t _{on}	Turn-on time	I _C =5A ; I _{B1} =1A I _{B2} =-2A V _{CC} =200V , R _L =40			0.5	μs
t _s	Storage time				2.5	μs
t _f	Fall time				0.3	μs

◆ h_{FE-1} Classifications

L	M	N
15-30	20-40	30-50

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PACKAGE OUTLINE

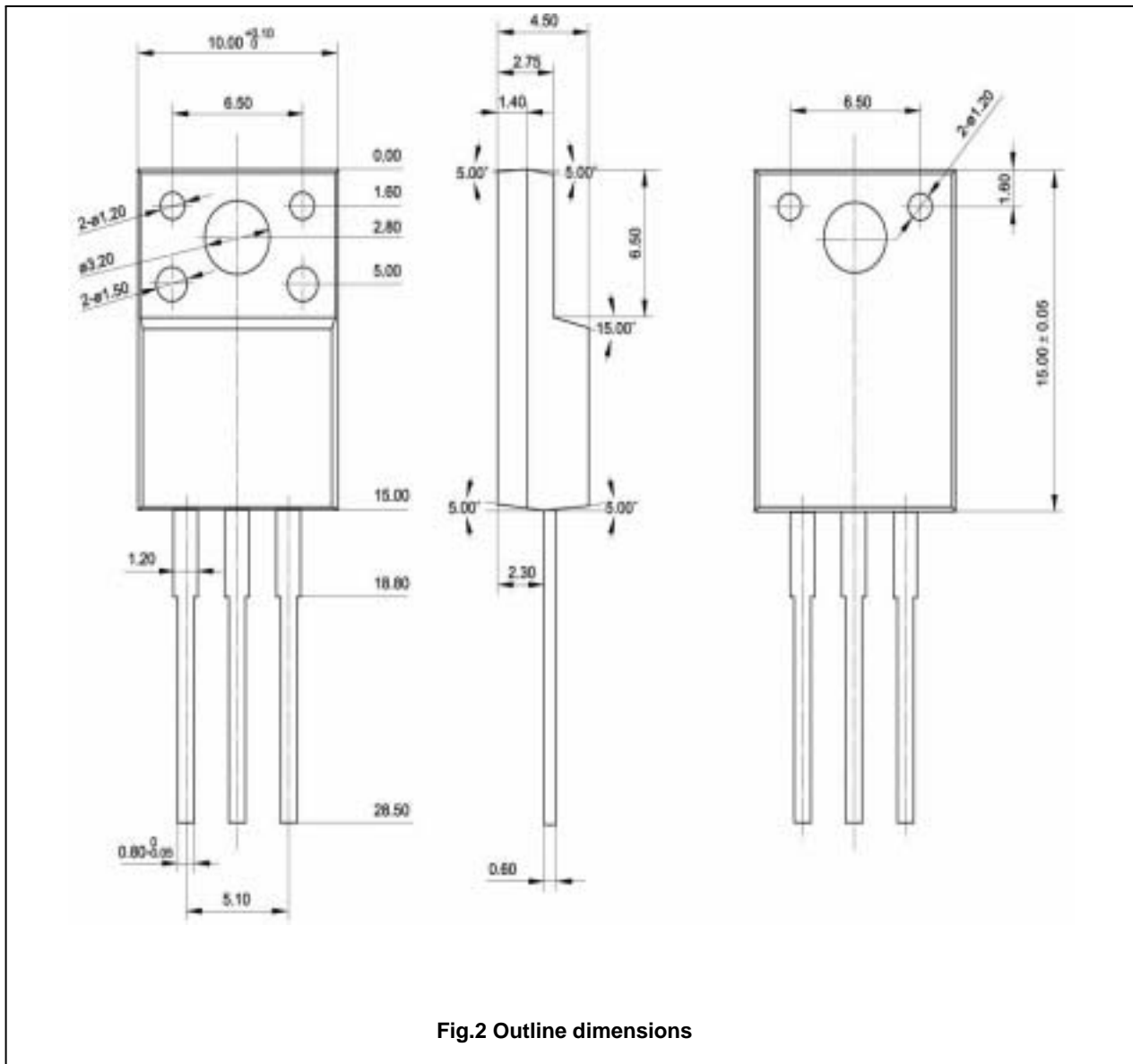


Fig.2 Outline dimensions

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